

film formed on a semiconductor device, scanning a laser beam which is intensity modulated at a desired frequency through a window and into the processing chamber where the semiconductor device is being processed by the plasma, receiving at a sensor back-scattered light from fine particles suspended in the processing chamber that are illuminated by the scanning laser beam, detecting the desired frequency component from a signal outputted from the sensor, obtaining information from the detected desired frequency component relating to quantity, size and distribution of fine particles illuminated by laser beam inside the processing chamber, and outputting the obtained information relating to quantity, size and distribution of the fine particles.

REMARKS

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the large number of corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience.

Applicants submit that the substitute specification includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.

The abstract has been amended to correct errors of a grammatical nature. A copy of the marked up abstract is enclosed.

Entry of the preliminary amendments and examination of

the application is respectfully requested.

To the extent necessary, applicant's petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 01-2135 (501.39474X00) and please credit any excess fees to such deposit account.

Respectfully submitted,



Melvin Kraus  
Registration No. 22,466  
ANTONELLI, TERRY, STOUT & KRAUS, LLP

MK/DRA/cee  
Attachments  
(703) 312-6600